NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **HF75-50S** is 50 V Class AB NPN Power transistor, designed for SSB & VHF Communacations.

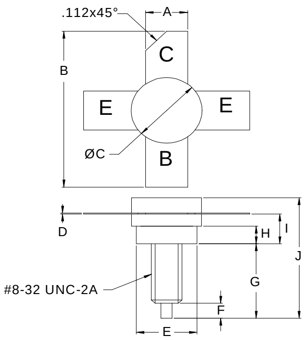
FEATURES INCLUDE:

- Direct Replacement for **TH513**
- High Gain, 16 dB Typical @ 30 MHz
- Withstands Server Mismatch
- ***Omnigold***™ Metalization System
- 75 W P_{OUT}
- 50 V OPERATIONS

MAXIMUM RATINGS

I_C	3.25 A
V_{CB}	110 V
V_{CE}	55 V
V_{EB}	4.0 V
P_{DISS}	127 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.0 °C/W

PACKAGE STYLE .380" 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

CHARACTERISTICS $T_C = 25\ ^{O}C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 100 mA	110			**V**
BV_{CEO}	I_C = 200 mA	55			**V**
BV_{EBO}	I_E = 10 mA	4.0			**V**
h_{FE}	V_{CE} = 6.0 V I_C = 1.4 A	19		50	**---**
C_{ob}	V_{CB} = 50 V f = 1.0 MHz			100	**pF**
G_{PE} **η_C** **IMD_3**	V_{CC} = 50 V P_{IN} = 3.0 W P_{OUT} = 75 WPEP f_1 = 30.000 MHz, f_2 = 30.001 MHz	14 37		 -30	**dB** **%** **dBc**